

#### What Is Claimed Is:

1. A planarization method comprising:
    - positioning a Group VIII metal-containing surface of a substrate to interface with a polishing surface, wherein the Group VIII metal is selected from the group of rhodium, iridium, ruthenium, osmium, palladium, platinum, and combinations thereof;
    - supplying a planarization composition in proximity to the interface; and
    - planarizing the Group VIII metal-containing surface; wherein the planarization composition comprises a complexing agent selected from the group of a cyclic diene, an organic amine, and combinations thereof.
  2. The method of claim 1 wherein the Group VIII metal is present in an amount of about 50 atomic percent or more.
  3. The method of claim 2 wherein the Group VIII metal-containing surface of the substrate comprises a Group VIII metal in elemental form or an alloy thereof.
  4. The method of claim 3 wherein the Group VIII metal-containing surface comprises elemental platinum or a platinum alloy.
  5. The method of claim 4 wherein the Group VIII metal-containing surface comprises elemental platinum.
  6. The method of claim 1 wherein the planarization composition further comprises an oxidizing agent.

7. The method of claim 6 wherein the oxidizing agent is selected from the group consisting of a peroxide, a nitrate, a permanganate, and a combination thereof.
- 5 8. The method of claim 1 wherein the polishing surface comprises a polishing pad and the planarization composition comprises a plurality of abrasive particles.
- 10 9. The method of claim 1 wherein the planarization composition comprises a plurality of abrasive particles having a hardness of no greater than about 9 Mohs.
- 15 10. The method of claim 9 wherein the plurality of abrasive particles comprise CeO<sub>2</sub>, Al<sub>2</sub>O<sub>3</sub>, SiO<sub>2</sub>, or combinations thereof.
11. The method of claim 1 wherein the substrate is a semiconductor substrate or substrate assembly.
- 20 12. The method of claim 1 wherein the Group VIII metal-containing surface is removed relative to an oxide layer at a selectivity ratio of at least about 10:1.
13. The method of claim 1 wherein the cyclic diene is selected from the group consisting of 1,5-cyclooctadiene (COD), 1,5-dimethyl-1,5-cyclooctadiene, and a combination thereof.
- 25 14. The method of claim 1 wherein the organic amine is selected from the group ethylamine, methylamine, triethylamine, trimethylamine, and combinations thereof.
15. The method of claim 1 wherein the polishing surface comprises a fixed abrasive article.

16. A planarization method comprising:
- positioning a Group VIII metal-containing surface of a substrate to interface with a polishing surface, wherein the Group VIII metal is selected from the group consisting of rhodium, iridium, ruthenium, osmium, palladium, platinum, and combinations thereof;
- supplying a planarization composition in proximity to the interface; and
- planarizing the Group VIII metal-containing surface;
- wherein the planarization composition comprises an organic amine and an organic chelating acid.
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17. The method of claim 16 wherein the Group VIII metal is present in an amount of about 50 atomic percent or more.
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18. The method of claim 16 wherein the Group VIII metal-containing surface comprises elemental platinum.
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19. The method of claim 16 wherein the planarization composition further comprises an oxidizing agent.
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20. The method of claim 19 wherein the oxidizing agent is selected from the group consisting of a peroxide, a nitrate, a permanganate, and a combination thereof.
21. The method of claim 16 wherein the polishing surface comprises a polishing pad and the planarization composition comprises a plurality of abrasive particles.

22. The method of claim 16 wherein the planarization composition comprises a plurality of abrasive particles having a hardness of no greater than about 9 Mohs.
- 5        23. The method of claim 22 wherein the plurality of abrasive particles comprise CeO<sub>2</sub>, Al<sub>2</sub>O<sub>3</sub>, SiO<sub>2</sub>, or combinations thereof.
24. The method of claim 16 wherein the substrate is a semiconductor substrate or substrate assembly.
- 10      25. The method of claim 16 wherein the organic chelating acid is selected from the group consisting of acetic acid, ascorbic acid, citric acid, propenoic acid, tartaric acid, succinic acid, and combinations thereof.
- 15      26. The method of claim 16 wherein the organic amine is selected from the group consisting of ethylamine, methylamine, triethylamine, trimethylamine, and combinations thereof.
- 20      27. The method of claim 16 wherein the polishing surface comprises a fixed abrasive article.
28. A planarization method comprising:  
positioning a Group VIII metal-containing surface of a substrate to interface with a polishing surface, wherein the Group VIII metal is selected from the group consisting of rhodium, iridium, ruthenium, osmium, palladium, platinum, and combinations thereof;  
supplying a planarization composition in proximity to the interface;  
and  
planarizing the Group VIII metal-containing surface;  
wherein the planarization composition comprises abrasive particles
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and a complexing agent; and further wherein a majority of the plurality of abrasive particles are CeO<sub>2</sub> abrasive particles.

29. The method of claim 28 wherein the Group VIII metal is present in an  
5 amount of about 50 atomic percent or more.
30. The method of claim 28 wherein the Group VIII metal-containing surface comprises elemental ruthenium.
- 10 31. The method of claim 28 wherein the planarization composition further comprises an oxidizing agent.
32. The method of claim 28 wherein the complexing agent is selected from the group consisting of an organic chelating acid, an organic amine, a cyclic  
15 diene, and combinations thereof.
33. The method of claim 32 wherein the organic chelating acid is selected from the group consisting of acetic acid, ascorbic acid, citric acid, propenoic acid, tartaric acid, succinic acid, and combinations thereof.  
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34. The method of claim 32 wherein the organic amine is selected from the group consisting of ethylamine, methylamine, triethylamine, trimethylamine, and combinations thereof.
- 25 35. The method of claim 32 wherein the cyclic diene is selected from the group consisting of 1,5-cyclooctadiene (COD), 1,5-dimethyl-1,5-cyclooctadiene, and a combination thereof.
36. The method of claim 28 wherein the polishing surface comprises a polishing pad.  
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37. A planarization method comprising:
- positioning a Group VIII metal-containing surface of a substrate to interface with a polishing surface, wherein the Group VIII metal is selected from the group consisting of rhodium, iridium, ruthenium, osmium, palladium, platinum, and combinations thereof;
- supplying a planarization composition in proximity to the interface; and
- planarizing the Group VIII metal-containing surface;
- wherein the planarization composition comprises a complexing agent selected from the group consisting of a cyclic diene, an organic amine, an organic chelating acid, and combinations thereof; and
- further wherein the method is carried out in one step.
- 15 38. The method of claim 37 wherein the planarization composition further comprises an oxidizing agent.
39. A planarization method comprising:
- providing a semiconductor substrate or substrate assembly including at least one region of a platinum-containing surface;
- providing a polishing surface;
- providing a planarization composition at an interface between the at least one region of platinum-containing surface and the polishing surface; and
- planarizing the at least one region of platinum-containing surface;
- wherein the planarization composition comprises a complexing agent selected from the group consisting of a cyclic diene, an organic amine, and combinations thereof.

40. The method of claim 39 wherein the planarization composition further comprises an oxidizing agent.
41. A planarization method comprising:  
5           providing a semiconductor substrate or substrate assembly including at least one region of a platinum-containing surface;  
             providing a polishing surface;  
             providing a planarization composition at an interface between the at least one region of platinum-containing surface and the polishing surface;  
10           and  
             planarizing the at least one region of platinum-containing surface;  
             wherein the planarization composition comprises an organic amine and an organic chelating acid.
- 15          42. The method of claim 41 wherein the planarization composition further comprises an oxidizing agent.
43. A planarization method comprising:  
20           providing a semiconductor substrate assembly including at least one region of a platinum-containing surface;  
             providing a polishing surface;  
             providing a planarization composition at an interface between the at least one region of platinum-containing surface and the polishing surface;  
             and  
25           planarizing the at least one region of platinum-containing surface;  
             wherein the planarization composition comprises abrasive particles and a complexing agent; and  
             further wherein a majority of the plurality of abrasive particles are CeO<sub>2</sub> abrasive particles.

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44. The method of claim 43 wherein the planarization composition further comprises an oxidizing agent.

45. The method of claim 43 wherein the polishing surface comprises a polishing pad.

46. A planarization method comprising:

providing a semiconductor substrate or substrate assembly including at least one region of a platinum-containing surface;

10 providing a polishing surface;

providing a planarization composition at an interface between the at least one region of platinum-containing surface and the polishing surface; and

planarizing the at least one region of platinum-containing surface;

15 wherein the planarization composition comprises a complexing agent selected from the group consisting of a cyclic diene, an organic amine, an organic chelating acid, and combinations thereof; and

further wherein the method is carried out in one step.

20 47. The method of claim 44 wherein the planarization composition further comprises an oxidizing agent.

48. A planarization method for use in forming a capacitor or barrier layer, the method comprising:

25 providing a semiconductor substrate or substrate assembly having a patterned dielectric layer formed thereon and a Group VIII metal-containing layer formed over the patterned dielectric layer, wherein the Group VIII metal is selected from the group consisting of rhodium, iridium, ruthenium, osmium, palladium, platinum, and combinations thereof;

30 positioning a first portion of a polishing surface for contact with the

Group VIII metal-containing layer;

providing a planarization composition in proximity to the contact between the polishing surface and the Group VIII metal-containing layer; and

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planarizing the Group VIII metal-containing layer;

wherein the planarization composition comprises a complexing agent selected from the group consisting of a cyclic diene, an organic amine, and combinations thereof.

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49. The method of claim 48 wherein the planarization composition further comprises an oxidizing agent.

50. A planarization method for use in forming a capacitor or barrier layer, the method comprising:

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providing a semiconductor substrate or substrate assembly having a patterned dielectric layer formed thereon and a Group VIII metal-containing layer formed over the patterned dielectric layer, wherein the Group VIII metal is selected from the group consisting of rhodium, iridium, ruthenium, osmium, palladium, platinum, and combinations thereof;

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positioning a first portion of a polishing surface for contact with the Group VIII metal-containing layer;

providing a planarization composition in proximity to the contact between the polishing surface and the Group VIII metal-containing layer;

and

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planarizing the Group VIII metal-containing layer;

wherein the planarization composition comprises an organic amine and an organic chelating acid.

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51. The method of claim 50 wherein the planarization composition further comprises an oxidizing agent.

52. A planarization method for use in forming a capacitor or barrier layer, the method comprising:

5 providing a semiconductor substrate or substrate assembly having a patterned dielectric layer formed thereon and a Group VIII metal-containing layer formed over the patterned dielectric layer, wherein the Group VIII metal is selected from the group consisting of rhodium, iridium, ruthenium, osmium, palladium, platinum, and combinations thereof;

10 positioning a first portion of a polishing surface for contact with the Group VIII metal-containing layer;

15 providing a planarization composition in proximity to the contact between the polishing surface and the Group VIII metal-containing layer;

and

planarizing the Group VIII metal-containing layer;

20 wherein the planarization composition comprises abrasive particles and a complexing agent; and

25 further wherein a majority of the plurality of abrasive particles are CeO<sub>2</sub> abrasive particles.

53. The method of claim 52 wherein the planarization composition further comprises an oxidizing agent.

54. The method of claim 52 wherein the polishing surface comprises a polishing pad.

55. A planarization method for use in forming a capacitor or barrier layer, the method comprising:

30 providing a semiconductor substrate or substrate assembly having a patterned dielectric layer formed thereon and a Group VIII metal-containing layer formed over the patterned dielectric layer, wherein the Group VIII metal is selected from the group consisting of rhodium, iridium, ruthenium,

osmium, palladium, platinum, and combinations thereof;  
positioning a first portion of a polishing surface for contact with the  
Group VIII metal-containing layer;  
providing a planarization composition in proximity to the contact  
5 between the polishing surface and the Group VIII metal-containing layer;  
and  
planarizing the Group VIII metal-containing layer;  
wherein the planarization composition comprises a complexing agent  
selected from the group consisting of a cyclic diene, an organic amine, an  
10 organic chelating acid, and combinations thereof; and  
further wherein the method is carried out in one step.

56. The method of claim 55 wherein the planarization composition further  
comprises an oxidizing agent.

15 57. The method of claim 55 wherein the polishing surface comprises a polishing  
pad.

20 58. The method of claim 55 wherein the polishing surface comprises a fixed  
abrasive article.